

## **General Description**

The WSP4016 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate chargens for most of the synchronous buck converter applications .

The WSP4016 meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

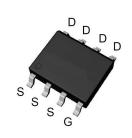
## **Product Summery**

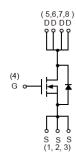
BVDSS	RDSON	ID
40V	11.5m $\Omega$	15.5A

### **Applicatio**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

## **SOP-8 Pin Configuration**





#### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	15.5	Α
I <sub>D</sub> @T <sub>C</sub> =70℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	8.4	Α
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup> 30		А
P <sub>D</sub> @T <sub>A</sub> =25℃	Total Power Dissipation T <sub>A</sub> =25°C	2.08	W
P <sub>D</sub> @T <sub>A</sub> =70°C	P <sub>D</sub> @T <sub>A</sub> =70 °C Total Power Dissipation T <sub>A</sub> =70 °C		W
T <sub>STG</sub>	Storage Temperature Range -55 t		$^{\circ}$
TJ	T <sub>J</sub> Operating Junction Temperature Range -5		°C

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit	
$R_{ heta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>		60	°C/W	
$R_{ heta JC}$	Thermal Resistance Junction-Case <sup>1</sup>		20	°C/W	

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature



## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	40			V	
В	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =7A		8.5	11.5	mΩ	
R <sub>DS(ON)</sub>		V <sub>GS</sub> =4.5V , I <sub>D</sub> =5A		11	14.5	1112.2	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250uA$	1.0	1.8	2.5	٧	
l	Drain Source Leakage Current	$V_{DS}$ =32V , $V_{GS}$ =0V , $T_J$ =25 $^{\circ}$ C			1	uA	
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =32V , $V_{GS}$ =0V , $T_{J}$ =55 $^{\circ}$ C			25		
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm20V$ , $V_{DS}$ = $0V$			±100	nA	
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =15A		31		S	
$Q_g$	Total Gate Charge (4.5V)	V <sub>DS</sub> =20V , V <sub>GS</sub> =10V ,		20	30		
Q <sub>gs</sub>	Gate-Source Charge			3.9		nC	
$Q_{gd}$	Gate-Drain Charge	I <sub>D</sub> =7A		3			
$T_{d(on)}$	Turn-On Delay Time	V <sub>DD</sub> =20V,V <sub>GEN</sub> =10V,		12.6			
T <sub>r</sub>	Rise Time	$R_G=1\Omega$ , $I_D=1A$ ,		10		20	
T <sub>d(off)</sub>	Turn-Off Delay Time	R <sub>L</sub> =20Ω.		23.6		ns	
T <sub>f</sub>	Fall Time	111-2012.		6			
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =20V ,		1125			
Coss	Output Capacitance	V <sub>GS</sub> =0V ,		132		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1MHz		70			

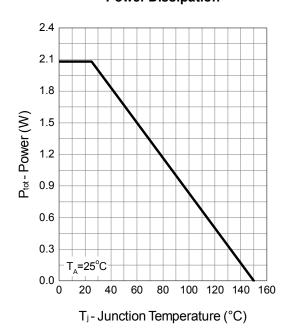
#### Note:

- 1. Pulse test: PW <= 300us duty cycle <= 2%.
- 2. Guaranteed by design, not subject to production testing.

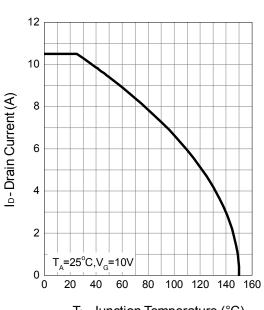


## **Typical Characteristics**

# Power Dissipation

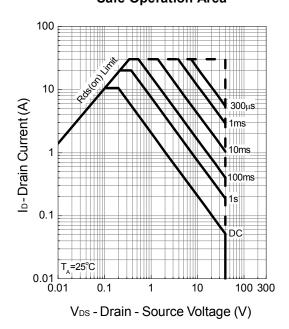


#### **Drain Current**

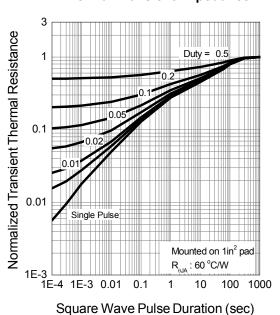


T<sub>j</sub>- Junction Temperature (°C)

## **Safe Operation Area**



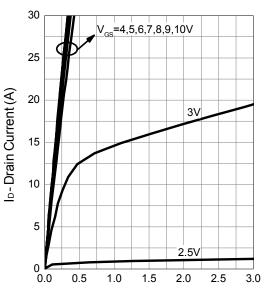
## **Thermal Transient Impedance**



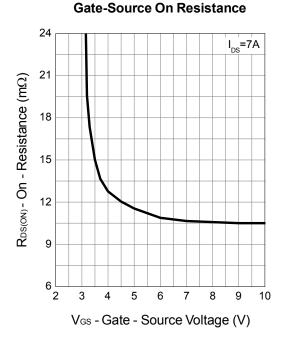


## **Typical Characteristics**

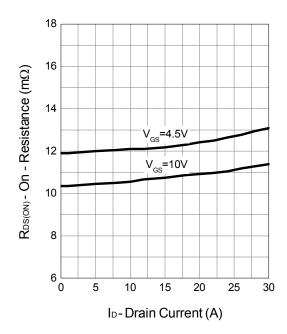
## **Output Characteristics**



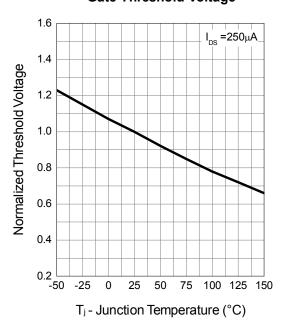
## V<sub>DS</sub> - Drain - Source Voltage (V)



#### **Drain-Source On Resistance**



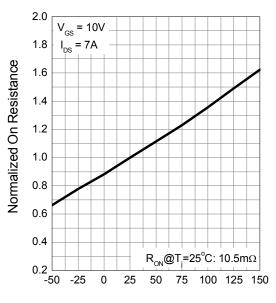
## **Gate Threshold Voltage**





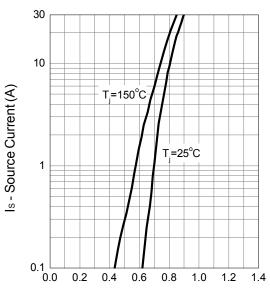
## **Typical Characteristics**

#### **Drain-Source On Resistance**



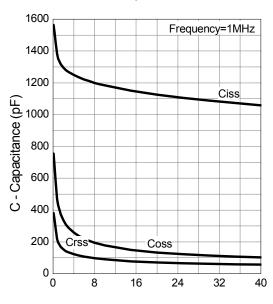
T<sub>j</sub>- Junction Temperature (°C)

#### **Source-Drain Diode Forward**



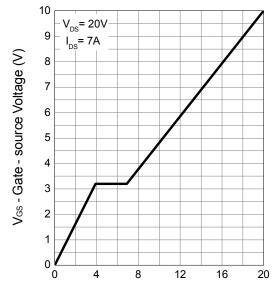
Vsp - Source - Drain Voltage (V)

## Capacitance



V<sub>DS</sub> - Drain - Source Voltage (V)

## **Gate Charge**

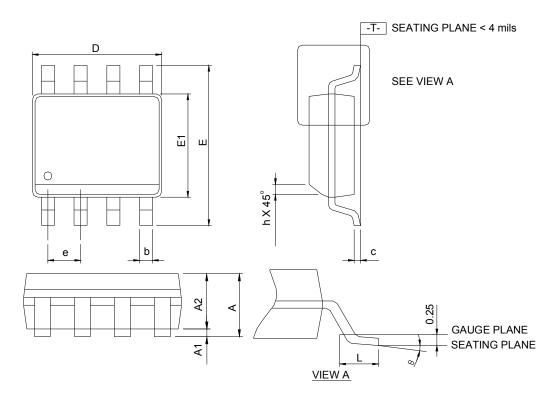


Q<sub>G</sub>-Gate Charge (nC)

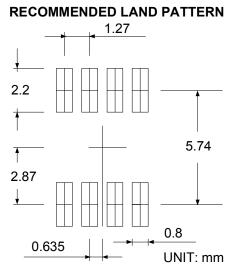


# **Package Information**

SOP-8



Ş	SOP-8			
\$\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	MILLIM	ETERS	INC	HES
P	MIN.	MAX.	MIN.	MAX.
Α	-	1.75	-	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	-	0.049	-
b	0.31	0.51	0.012	0.020
С	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
Е	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050	) BSC
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°



Note: 1. Follow JEDEC MS-012 AA.

- 2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
- 3. Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.



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